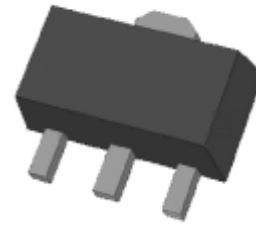


SOT-89 Medium Power Transistor PNP

FEATURES

- High breakdown voltage
- Complements to 2SD1767
- SOT-89 Package



1base 2collector 3emitter

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-80	Vdc
Collector-Base Voltage	V_{CBO}	-80	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current—Continuous	I_C	-0.7	Adc
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS

($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Type	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$	—	—	-0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$	—	—	-0.5	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=2.0\text{mA}$	-80	—	—	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}$	-80	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-5\mu\text{A}$	-5	—	—	V
DC Current Gain	h_{FE}	$V_{CE}=-3\text{V}, I_C=-100\text{mA}$	82	—	390	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$	—	—	-0.4	—
Transition Frequency	f_T	$V_{CE}=10\text{V}, I_E=-50\text{mA}, f=100\text{MHz}$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$	—	20	—	pF

Typical Characteristics

